



Docket No.: M4065.0700/P700-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Terry L. Gilton, et al.

Application No.: 10/634,897

Filed: August 6, 2003

Art Unit: N/A

For: METHODS OF FORMING NON-
VOLATIVE RESISTANCE VARIABLE
DEVICES AND METHODS OF
FORMING SILVER SELENIDE
COMPRISING STRUCTURES

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed within three months of the U.S. filing date (37 CFR 1.97(b)(1)).

Those patent(s) or publication(s) which are marked with an asterisk (*) next to the Cite No. in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application number 10/061,825, filed January 31, 2002 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

A concise explanation of relevance of the items not marked by asterisk and listed on form PTO/SB/08 is in the form of an English language copy of a Search Report from a foreign patent office, issued in a counterpart application, which refers to the relevant portions of the references.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0700/P700-A. A duplicate copy of this paper is enclosed.

Dated: November 5, 2003

Respectfully submitted,

By 

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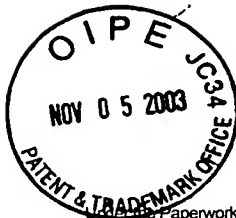
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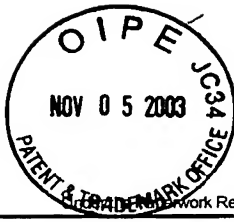
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				C mplete if Kn wn	
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-6,117,720	09/12/2000	Harshfield	
	AB	US-3,450,967	06/17/1969	Tolutis	
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Sheet	2	of	11	Attorney Docket Number	M4065.0700/P700-A

*	p	US-2003/0027416 APP	2/6/2003	Moore	
*	q	US-2003/0001229 APP	1/2/2003	Moore et al.	
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*	A9	US-09/943,187		Campbell et al. (as filed)	
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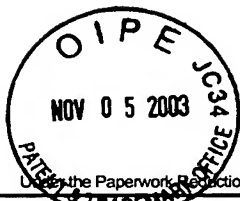
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*	A29	US-5,512,328	04/1996	Yoshimura et al.		
*	A30	US-6,117,720	09/2000	Harshfield		
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	WO 97/48032	12/18/1997	Kozicki et al.		
*	BB	WO 99/28914	06/10/1999	Kozicki et al.		
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*	BE	02/21542 A1	13/03/2002	WIPO (Kozicki et al.)		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

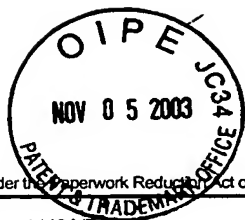
NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
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*	CN	SOMOGYI et al., "Temperature Dependence of the Carrier Mobility in Ag ₂ Se Layers Grown on NaCl and SiO ₂ Substrates, 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255, 1994.
*	CO	TAI et al., "Multilevel Ge-Se film based resist systems," SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 32-39, March 1982.
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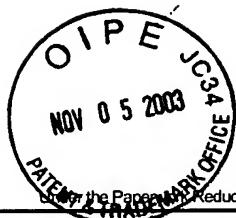


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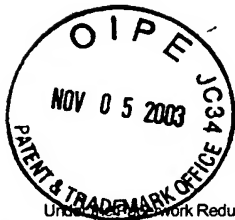
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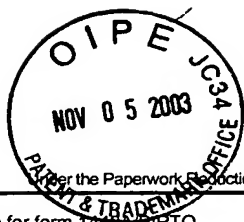
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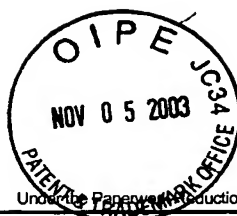
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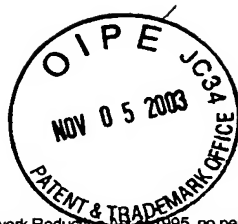
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